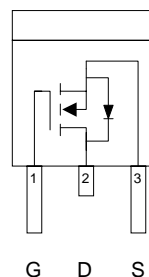


N-Channel Enhancement Mode MOSFET

Features

- 20V/6A , $R_{DS(ON)}=35m\Omega(\text{typ.}) @ V_{GS}=4.5V$
 $R_{DS(ON)}=38m\Omega(\text{typ.}) @ V_{GS}=2.5V$
- Super High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged
- TO-252 Package

Pin Description




Applications

Top View of TO-252

- Power Management in Computer, Portable Equipment and Battery Powered Systems.

Ordering and Marking Information

| | |
|--|---|
| <p>APM2030N □□-□□</p> <div style="margin-left: 20px;"> <p>└─── Handling Code</p> <p>└─── Temp. Range</p> <p>└─── Package Code</p> </div> | <p>Package Code U : TO-252</p> <p>Operation Junction Temp. Range C : -55 to 150°C</p> <p>Handling Code TR : Tape & Reel</p> |
| <p>APM2030N U :</p> <div style="display: inline-block; border: 1px solid black; padding: 2px; margin-left: 10px;">  <p>APM2030N XXXXXX</p> </div> | <p>XXXXXX - Date Code</p> |

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Rating | Unit |
|-----------|----------------------|----------|------|
| V_{DSS} | Drain-Source Voltage | 20 | V |
| V_{GSS} | Gate-Source Voltage | ± 10 | |

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Rating | Unit | |
|-----------------|--|-------------------------|--------------------|---|
| I_D^* | Maximum Drain Current – Continuous | 20 | A | |
| I_{DM} | Maximum Drain Current – Pulsed | 40 | | |
| P_D | Maximum Power Dissipation | $T_A=25^\circ\text{C}$ | 50 | W |
| | | $T_A=100^\circ\text{C}$ | 10 | |
| T_J | Maximum Junction Temperature | 150 | $^\circ\text{C}$ | |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ | |
| $R_{\theta JA}$ | Thermal Resistance – Junction to Ambient | 50 | $^\circ\text{C/W}$ | |

* Surface Mounted on FR4 Board, $t \leq 10$ sec.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

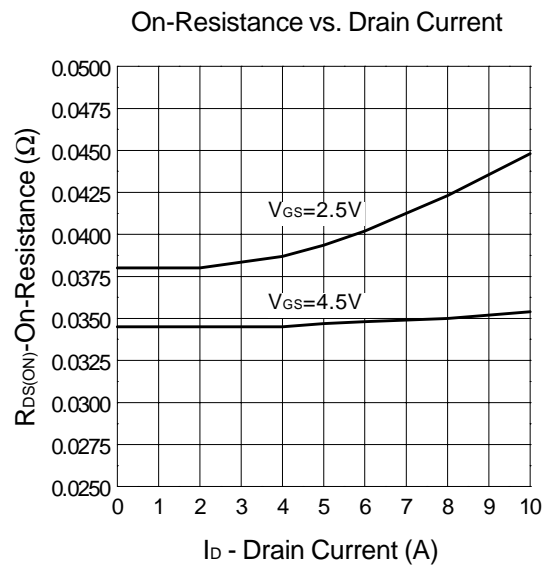
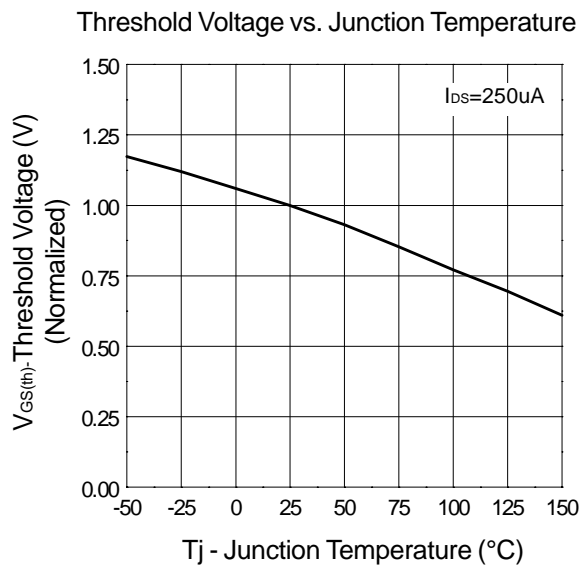
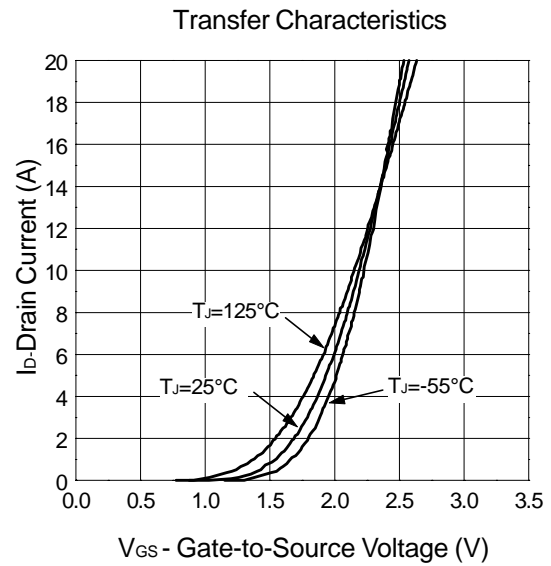
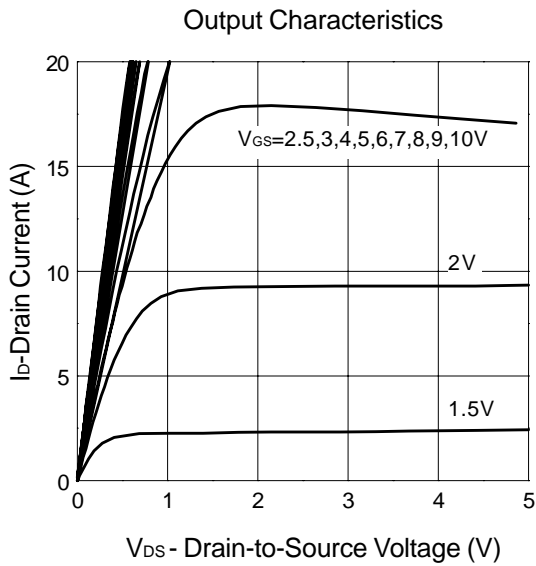
| Symbol | Parameter | Test Condition | APM2030N | | | Unit |
|----------------------------|----------------------------------|---|----------|------|-----------|---------------|
| | | | Min. | Typ. | Max. | |
| Static | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_{DS}=250\mu\text{A}$ | 20 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=18V, V_{GS}=0V$ | | | 1 | μA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$ | 0.5 | | 1.5 | V |
| I_{GSS} | Gate Leakage Current | $V_{GS}=\pm 10V, V_{DS}=0V$ | | | ± 100 | nA |
| $R_{DS(ON)}^a$ | Drain-Source On-state Resistance | $V_{GS}=4.5V, I_{DS}=6A$ | | 35 | 40 | m Ω |
| | | $V_{GS}=2.5V, I_{DS}=2A$ | | 38 | 50 | |
| V_{SD}^a | Diode Forward Voltage | $I_{SD}=4A, V_{GS}=0V$ | 0.6 | | 1.3 | V |
| Dynamic^b | | | | | | |
| Q_g | Total Gate Charge | $V_{DS}=10V, I_{DS}=5A$ $V_{GS}=4.5V,$ | | 9 | 18 | nC |
| Q_{gs} | Gate-Source Charge | | | 3.6 | | |
| Q_{gd} | Gate-Drain Charge | | | 1 | | |
| $t_{d(ON)}$ | Turn-on Delay Time | $V_{DD}=10V, I_{DS}=1A,$ $V_{GEN}=4.5V, R_G=0.2\Omega$ | | 17 | | ns |
| T_r | Turn-on Rise Time | | | 15 | | |
| $t_{d(OFF)}$ | Turn-off Delay Time | | | 45 | | |
| T_f | Turn-off Fall Time | | | 25 | | |
| C_{iss} | Input Capacitance | $V_{GS}=0V$ | | 520 | | pF |
| C_{oss} | Output Capacitance | $V_{DS}=15V$ | | 110 | | |
| C_{rss} | Reverse Transfer Capacitance | Frequency=1.0MHz | | 70 | | |

Notes

^a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

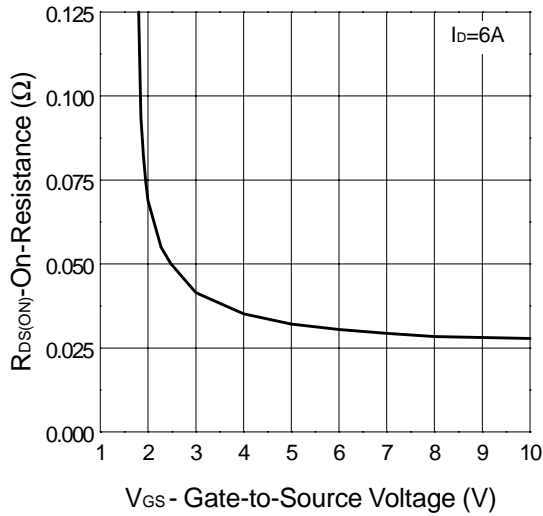
^b : Guaranteed by design, not subject to production testing

Typical Characteristics

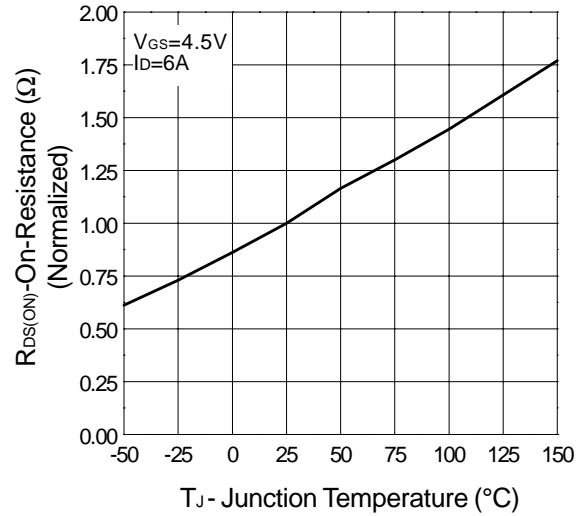


Typical Characteristics

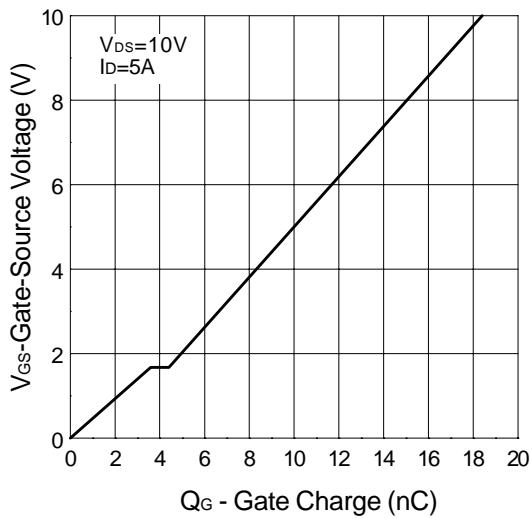
On-Resistance vs. Gate-to-Source Voltage



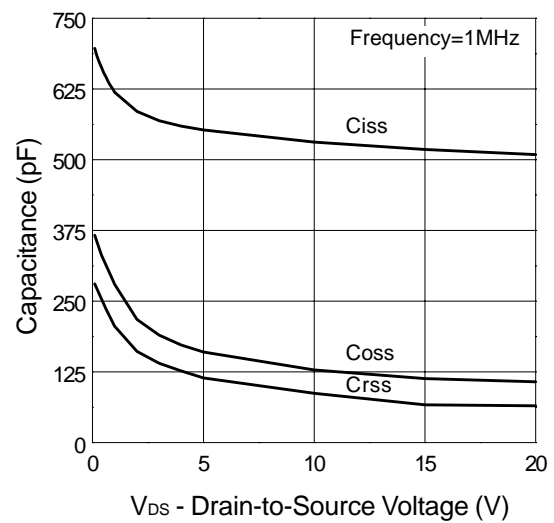
On-Resistance vs. Junction Temperature



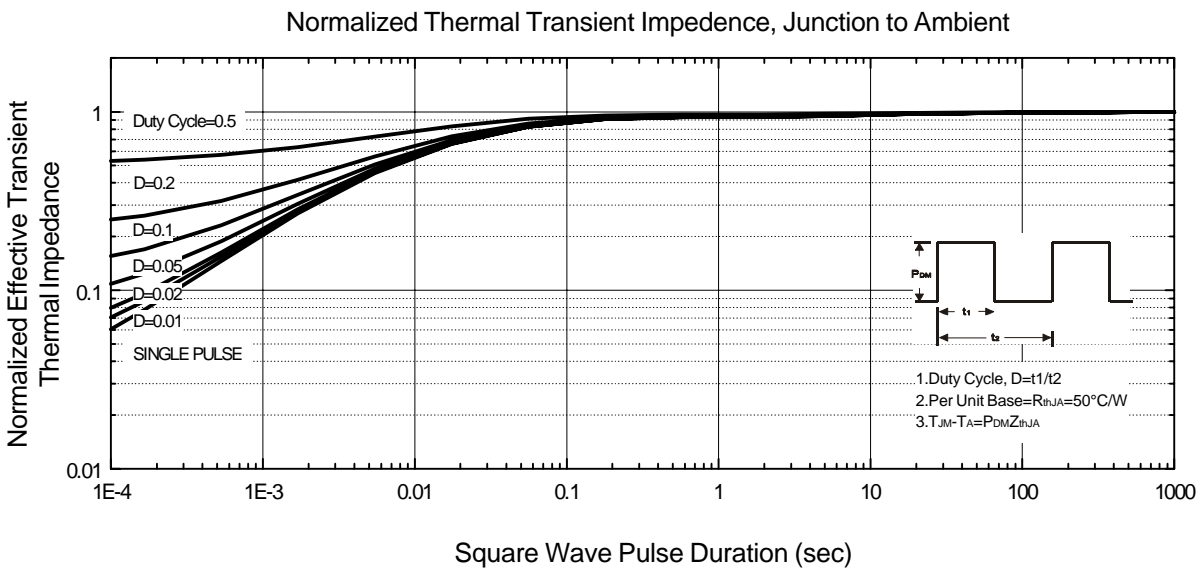
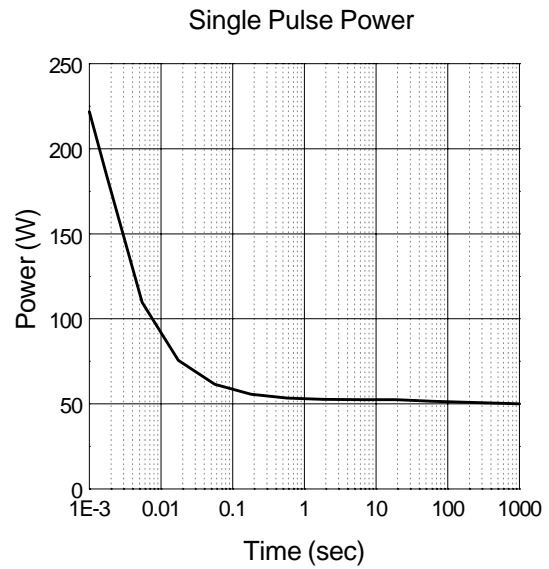
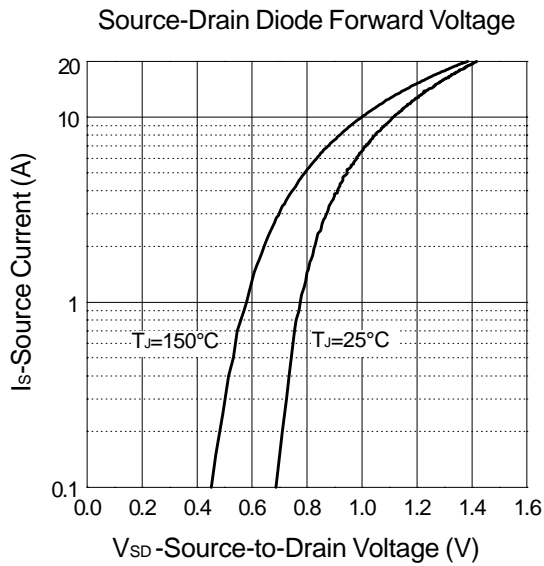
Gate Charge



Capacitance

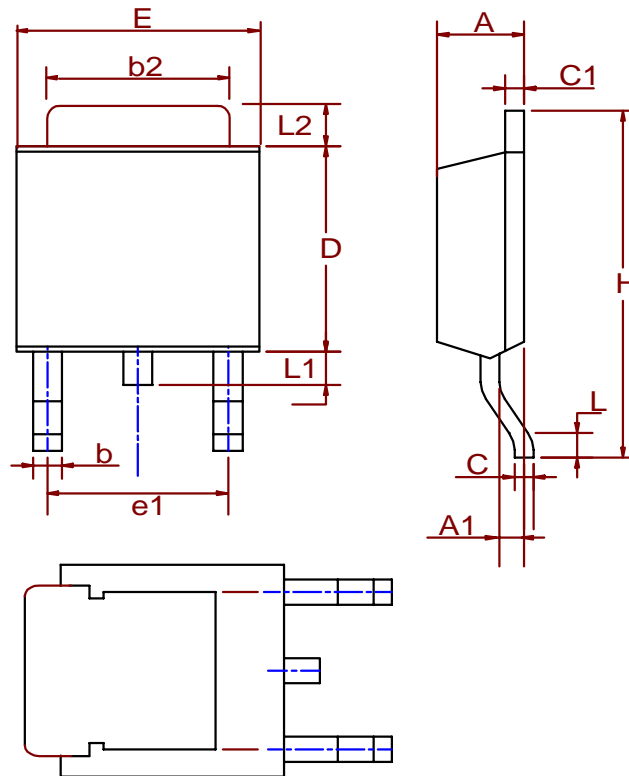


Typical Characteristics



Packaging Information

TO-252(Reference JEDEC Registration TO-252)

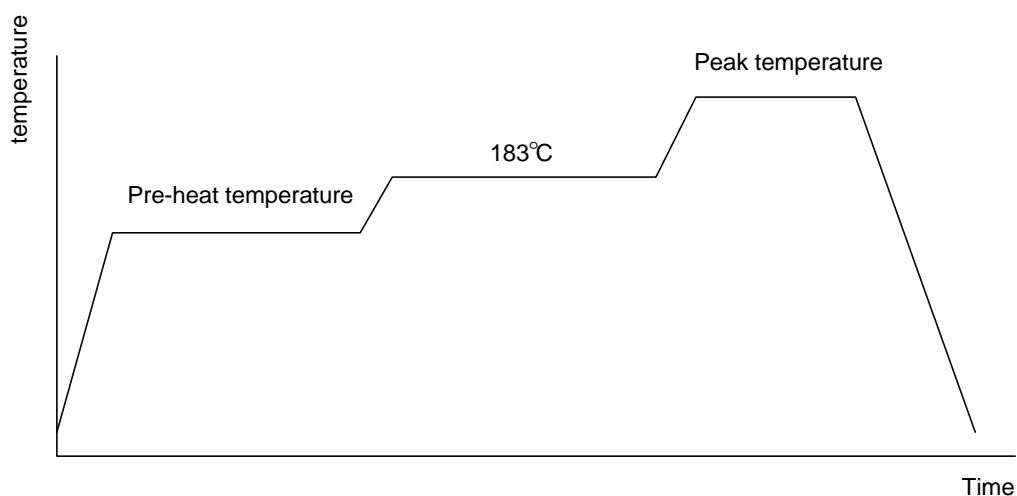


| Dim | Millimeters | | Inches | |
|-----|-------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.18 | 2.39 | 0.086 | 0.094 |
| A1 | 0.89 | 1.27 | 0.035 | 0.050 |
| b | 0.508 | 0.89 | 0.020 | 0.035 |
| b2 | 5.207 | 5.461 | 0.205 | 0.215 |
| C | 0.46 | 0.58 | 0.018 | 0.023 |
| C1 | 0.46 | 0.58 | 0.018 | 0.023 |
| D | 5.334 | 6.22 | 0.210 | 0.245 |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| e1 | 3.96 | 5.18 | 0.156 | 0.204 |
| H | 9.398 | 10.41 | 0.370 | 0.410 |
| L | 0.51 | | 0.020 | |
| L1 | 0.64 | 1.02 | 0.025 | 0.040 |
| L2 | 0.89 | 2.032 | 0.035 | 0.080 |

Physical Specifications

| | |
|--------------------|--|
| Terminal Material | Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb) |
| Lead Solderability | Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3. |

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

| | Convection or IR/ Convection | VPR |
|--|---------------------------------|--------------------------|
| Average ramp-up rate(183°C to Peak) | 3°C/second max. | 10 °C /second max. |
| Preheat temperature 125 ± 25°C) | 120 seconds max | |
| Temperature maintained above 183°C | 60 – 150 seconds | |
| Time within 5°C of actual peak temperature | 10 –20 seconds | 60 seconds |
| Peak temperature range | 220 +5/-0°C or 235 +5/-0°C | 215-219°C or 235 +5/-0°C |
| Ramp-down rate | 6 °C /second max. | 10 °C /second max. |
| Time 25°C to peak temperature | 6 minutes max. | |

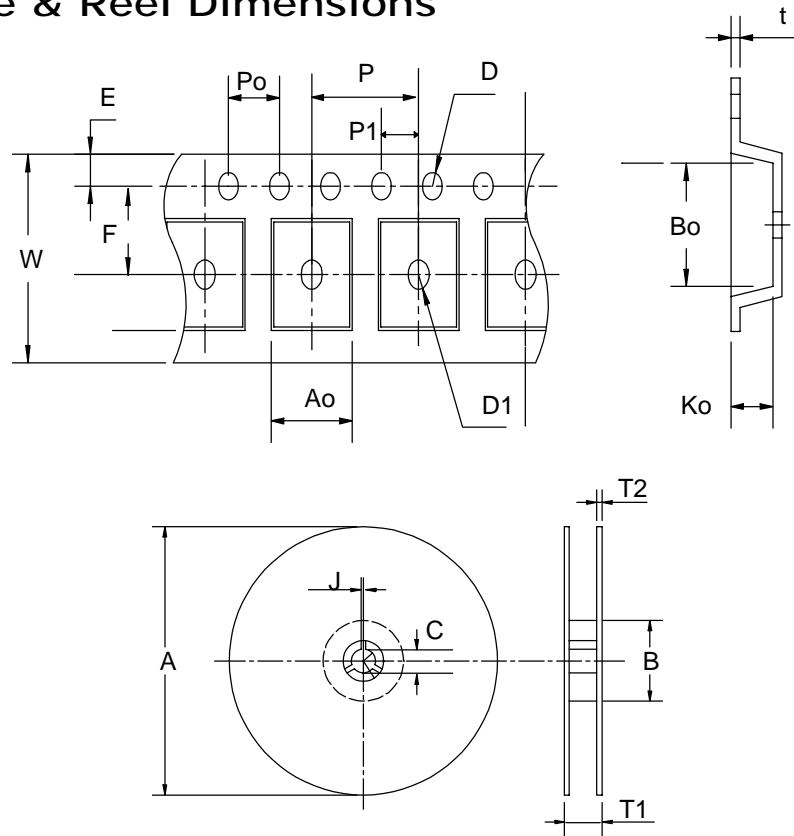
Package Reflow Conditions

| pkg. thickness ≥ 2.5mm and all bgas | pkg. thickness < 2.5mm and pkg. volume ≥ 350 mm ³ | pkg. thickness < 2.5mm and pkg. volume < 350mm ³ |
|--|---|--|
| Convection 220 +5/-0 °C | | Convection 235 +5/-0 °C |
| VPR 215-219 °C | | VPR 235 +5/-0 °C |
| IR/Convection 220 +5/-0 °C | | IR/Convection 235 +5/-0 °C |

Reliability test program

| Test item | Method | Description |
|---------------|---------------------|---------------------------|
| SOLDERABILITY | MIL-STD-883D-2003 | 245°C, 5 SEC |
| HOLT | MIL-STD 883D-1005.7 | 1000 Hrs Bias @ 125°C |
| PCT | JESD-22-B, A102 | 168 Hrs, 100% RH, 121°C |
| TST | MIL-STD 883D-1011.9 | -65°C ~ 150°C, 200 Cycles |

Carrier Tape & Reel Dimensions



| Application | A | B | C | J | T1 | T2 | W | P | E |
|-------------|-----------|-----------|------------|-----------|-------------------|-----------|-----------------|-----------|------------|
| TO-252 | 330 ± 3 | 100 ± 2 | 13 ± 0.5 | 2 ± 0.5 | 16.4 +0.3 -0.2 | 2.5 ± 0.5 | 16 +0.3 -0.1 | 8 ± 0.1 | 1.75 ± 0.1 |
| | F | D | D1 | Po | P1 | Ao | Bo | Ko | t |
| | 7.5 ± 0.1 | 1.5 ± 0.1 | 1.5 ± 0.25 | 4.0 ± 0.1 | 2.0 ± 0.1 | 6.8 ± 0.1 | 10.4 ± 0.1 | 2.5 ± 0.1 | 0.3 ± 0.05 |

Cover Tape Dimensions

| Application | Carrier Width | Cover Tape Width | Devices Per Reel |
|-------------|---------------|------------------|------------------|
| TO- 252 | 16 | 13.3 | 2500 |

Customer Service

Anpec Electronics Corp.

Head Office :

5F, No. 2 Li-Hsin Road, SBIP,

Hsin-Chu, Taiwan, R.O.C.

Tel : 886-3-5642000

Fax : 886-3-5642050

Taipei Branch :

7F, No. 137, Lane 235, Pac Chiao Rd.,

Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.

Tel : 886-2-89191368

Fax : 886-2-89191369